

# **isc Silicon NPN Power Transistor**

# 2SD1412

### DESCRIPTION

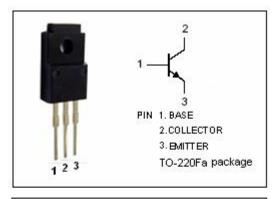
- Low Collector Saturation Voltage
  : V<sub>CE(sat)</sub>= 0.4V(Max)@ I<sub>C</sub>= 4A
- Collector-Emitter Breakdown Voltage-
  - : V<sub>(BR)CEO</sub>= 50V (Min)
- Complement to Type 2SB1019
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

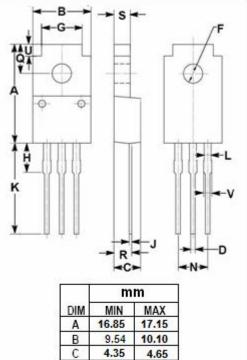
#### **APPLICATIONS**

- High current switching applications.
- Power amplifier applications.

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	Collector-Base Voltage	70	V
V <sub>CEO</sub>	Collector-Emitter Voltage	50	V
Vево	Emitter-Base Voltage	5	V
lc	Collector Current-Continuous	7	A
I <sub>B</sub>	Base Current-Continuous	1	A
Pc	Collector Power Dissipation @ T <sub>a</sub> =25℃	2	14/
	Collector Power Dissipation @ T <sub>c</sub> =25°C	30	W
TJ	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature Range	-55~150	°C

## ABSOLUTE MAXIMUM RATINGS(Ta=25°C)





D

F

G

н

J K

L

Ν

Q

R

S

0.75

3.20

6.90

5.15

0.45

13.35

1.10

4.98

4.85

2.55

2.70

0.90

3.40

7.20

5.45

0.75

13.65

5.18

5.15

3.25

2.90

isc website: <u>www.iscsemi.com</u>



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## **ELECTRICAL CHARACTERISTICS**

#### $T_{\text{C}}\text{=}25\,^{\circ}\!\!\!\!\!\!\mathrm{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 30mA ; I <sub>B</sub> = 0	50			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 4A; I <sub>B</sub> = 0.4A			0.4	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 4A; I <sub>B</sub> = 0.4A			1.2	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 70V; I <sub>E</sub> = 0			30	μA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			50	μA
h <sub>FE-1</sub>	DC Current Gain	Ic= 1A; Vc= 1V	70		240	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 4A; V <sub>CE</sub> = 1V	30			
С <sub>ОВ</sub>	Output Capacitance	I <sub>E</sub> = 0; V <sub>CB</sub> = 10V, f <sub>test</sub> = 1MHz		250		pF
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> = 1A; V <sub>CE</sub> = 4V		10		MHz

Switching Times

t <sub>on</sub>	Turn-on Time		0.2	μ <b>s</b>
t <sub>stg</sub>	Storage Time	I <sub>B1</sub> = I <sub>B2</sub> = 0.3A; R <sub>L</sub> = 10 Ω ; V <sub>CC</sub> = 30V	2.5	μs
t <sub>f</sub>	Fall Time		0.5	μ <b>S</b>

### hFE classifications

0	Y	
70-140	120-240	

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